Program

3/8 (Sun)

18:00-19:30	Welcome Party at Hotel Castle Plaza

3/9 (Mon)

9:00-9:10	Opening Opening Address M. Matsuo, President of Aichi Science & Technology Foundation Opening Remarks M. Hori, Chairperson of the Organizing Committee	
9:10-9:30	The Second Stage Knowledge Cluster Initiative (Chair: S. Noda)	O. Takenaka Aichi Science & Technology Foundation (ASTF), Japan Tokai Region Nanotechnology Manufacturing Cluster Innovation of Environment-Friendly High-Level Functional Materials and Devices Leading the World
9:30-10:10		M. Hori Nagoya University, Japan Advanced Plasma Fundamental Nanotechnology
10:10-10:30		Break
10:30-11:00		O. Takai Nagoya University, Japan Development of Nanomaterials with Novel Surface Function
11:00-11:30		T. Egawa Nagoya Institute of Technology, Japan High-efficient Optical, Power Materials and Devices
11:30-12:00		Y. Watanabe Nagoya Institute of Technology, Japan Development of Nanocomposites Based on Interface Engineering -Collaboration with Other Relevant Ministries-
12:00-14:00	Lunch and Poster Session I	
14:00-14:30	Plasma (1) Plasma Researches in Advanced Plasma Nanoprocessing Research Affiliations (Chair: K. Nakamura)	J.G. Han, Y.S. Choi, A. Matilainen, and S.B. Jin Sungkyunkwan University, Korea Low Temperature Synthesis of SiO_2 on Polymer Substrate by PECVD
14:30-15:00		U. Czarnetzki[1], B.G. Heil[1], J. Schulze[1], Z. Donko[2], R.P. Brinkmann[1], and Th. Mussenbrock[1] [1]Ruhr-University, Germany [2]Hungarian Academy of Science, Hungary A Novel Technique for Independent Control of Ion Energy and Flux in CCPs
15:00-15:30		M.J. Goeckner, C.T. Nelson, S.P. Sant, A.K. Jindal, E. Joseph, B-S. Zhou, G. Padron-Wells, B. Jarvis, C. Estrada, D. Urrabazo, R. Pierce, and L.J. Overzet The University of Texas at Dallas, U.S.A. Plasma-surface Interactions
15:30-15:40	Break	
15:40-16:10	Plasma (2) Present Status and Perspectived in Advanced Plasma Nanomaterial Processing (Chair: Y. Watanabe)	G. Cunge[1], E. Pargon[1], O. Joubert[1], L. Vallier[1], T. Chevolleau[1], R. Ramos[1], E. Sungauer[1], M. Martin[1], O. Luere[1], S. Barnola[2], T. Morel[2], and T. Lill[3] [1]CNRS, France [2]CEA-LETI, France [3]Applied Materials, Sunnyvale, U.S.A. Challenges and Future Prospects in Plasma Etching
16:10-16:40		J. Musil[1,2] and P. Baroch[1] [1]University of West Bohemia, Czech Republic [2]Academy of Sciences of the Czech Republic, Czech Republic Advanced Sputtering Discharges for Thin Film Deposition
16:40-17:10		S. Hosaka Tokyo Electron Ltd., Japan Current R&D Status and Prospects of Si Semiconductor Plasma Processing Equipment System
17:30-19:00	Banquet Restaurant Hananoki in Nagoya University	

3/10 (Tue)

9:00-9:20	Towards the Development of Autonomic MBE Systems Based on Nitride Radical Sources and Radical Monitoring (Chair: K. Hiramatsu)	M. Hori Nagoya University, Japan Application of Advanced Plasma Technology for the Development of Autonomic MBE System
9:20-9:45		B. Daudin CEA-Grenoble, INAC/SP2M, France Growth of GaN Heterostructures by Plasma-assisted Molecular Beam Epitaxy
9:45-10:10		Y. Nanishi and T. Yamaguchi Ritsumeikan University, Japan Proposal of New InN Growth Method by MBE and Usefulness of This Method as Nitrogen Radical Beam Monitoring
10:10-10:30		Break
10:30-10:55		A. Yoshikawa, Y. Ishitani, N. Hashimoto, H. Saito, and S. Che Chiba University, Japan Self-limiting Growth of -1ML-thick InN on Ga-polarity GaN by rf-plasma MBE
10:55-11:20		J.Y. Duboz, F. Semond, Y. Cordier, and J. Massies CRHEA-CNRS, France MBE Epitaxy of GaN on Si
11:20-11:45		K. Kishino[1,2,3], H. Sekiguchi[1,3], and A. Kikuchi[1,2,3] [1]Sophia University, Japan [2]Sophia Nanotechnology Research Center, Japan [3]CREST, Japan Science and Technology Agency, Japan Regularly Arranged InGaN-based Nanocolumns and their Emission Color Control over Full Visible Range
11:45-12:00		H. Amano Meijo University, Japan Expectation for Nitride-based Nanostructure for Future Light Emitting Devices
12:00-14:00	Lunch and Poster Session II	
14:00-14:30	Towards the Advanced Plasma Nanotechnology Science and Research Foundation (with interpretation) (Chair: M. Sekine)	J.C. Guibert CEA, MINATEC, France MINATEC, A New Research Campus Concept for Nanoscience and Technology
14:30-15:00		C.D. Dilks Philadelphia Science Center, U.S.A. Technology-LED Economic Development -Changing Tactics to Meet Desire Outcomes Science Center in Philadelphia, Pennsylvania – A Case Study
15:00-15:30		M. Kume PLACIA, Nagoya Urban Industries Promotion Corporation, Japan Activities of Plasma Technology Transfer to Industries in PLACIA
15:30-15:50	Break	
15:50-17:00	Panel Discussion (with interpretation)	〜Technology Transfer; Scheme and Management〜 Moderator O. Takenaka, ASTF Panelists M. Hori, Nagoya University, Japan J.G. Han, Sungkyunkwan University, Korea J.C. Guibert, MINATEC, France C.D. Dilks, Philadelphia Science Center, U.S.A. M. Kume, PLACIA, Japan K. Matsumoto, TN EMC Ltd., Japan

3/11 (Wed)

9:00-9:20	Plasma (3) The Front of Radical Control Plasma Nanoprocessing Research (Chair: H. Toyoda)	T. Hara, R. Ichiki, and Y. Kubota Toyota Technological Institute, Japan Modification of Metal Surface by Atomic Nitrogen
9:20-9:40		M. Hiramatsu Meijo University, Japan Carbon Nanowall Fabrication by Radical-Controlled Plasma Processing: Toward the Application for New Functional Devices
9:40-10:00		M. Shiratani[1], S. Iwashita[1], H. Miyata[1], H. Matsuzaki[1], K. Koga[1], and M. Akiyama[2] [1]Kyushu University, Japan [2]Advanced Industrial Science and Technology (AIST), Japan Plasma Manipulation of Nano-blocks and its Application to ULK Film Deposition
10:00-10:30	Break	
10:30-10:50	Plasma (4) The Front of Flexible Electronics Researches (Chair: M. Hiramatsu)	Y. Setsuhara[1, 4], K. Cho[1], K. Takenaka[1, 4], M. Shiratani[2, 4], M. Sekine[3, 4], and M. Hori[3, 4] [1]Osaka University, Japan [2]Kyushu University, Japan [3]Nagoya University, Japan [4]JST, CREST, Japan Production and Control of Low-Damage Large-Area Plasmas for Advanced Processing of Next-Generation Devices
10:50-11:10		K. Nakamura and H. Sugai Chubu University, Japan Development of Electron-Based Plasma Monitoring for Precise Control of Plasma Process
11:10-11:30		A. Wakahara, H. Okada, and Y. Furukawa Toyohashi University of Technology, Japan Nitride-based Optoelectronic Integrated Devices
11:30-11:50		H. Toyoda Nagoya University, Japan Low Temperature Microcrystalline Silicon Film Deposition by Microwave High-density Plasma
11:50-12:10		H. Kousaka and N. Umehara Nagoya University, Japan Novel DLC Synthesis Method Employing High-density Plasma sustained by Microwave Propagation along Plasma-sheath Interface

12:10-12:20	Closing Closing Remarks M. Hori, Chairperson of the Organizing Committee